

Product / Process Change Notice

Parts Affected:

Chip process CP517, PNP silicon, Darlington power transistors, wafers, and bare die.

Extent of Change:

The CP517 wafer process has been discontinued and replaced with the CP527 wafer process.

The overall wafer diameter is being reduced from 5 inch to 4 inch.

The die pattern has been changed; see figures 1 and 2 for details.

Reason for Change:

This process was transferred to an alternate wafer foundry due to low volume production.

Effect of Change:

The wafer process meets all electrical specifications of the individual devices listed on the following page.

Qualification:

Standard evaluation and qualifications completed resulting in no performance degradation.

Effective Date of Change:

Existing inventory will be shipped until depleted.

Sample Availability:

Please contact Salesperson or Manufacturer's Representative.

Figures:

Figure 1: CP517 Chip Geometry (Discontinued)

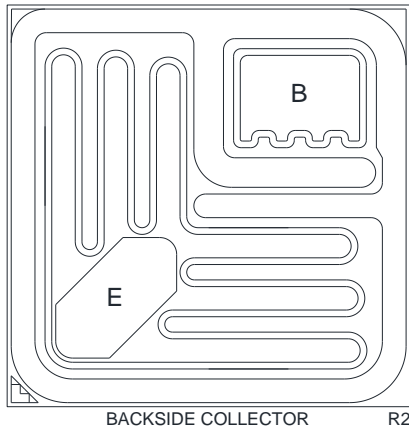
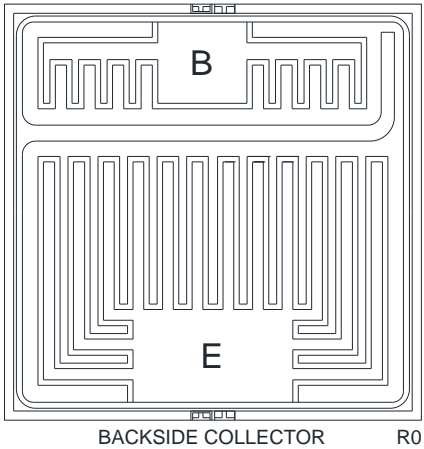


Figure 2: CP527 Chip Geometry



Wafer Diameter: 5 inch
Die Size: 111 x 111 mils
Die Thickness: 11 mils
Bond Pad Size (Emitter): 20 x 26 mils
Bond Pad Size (Base): 20 x 30 mils
Topside Metal: Al (60,000Å)
Backside Metal: Au/Cr/Ni/Au (6,100Å)

Wafer Diameter: 4 inch
Die Size: 110 x 110 mils
Die Thickness: 10.6 mils
Bond Pad Size (Emitter): 24 x 42 mils
Bond Pad Size (Base): 21 x 24 mils
Topside Metal: Al (20,000Å)
Backside Metal: Ag (10,000Å)

Part Numbers Affected:

2N6296	CP517-2N6042-CT
2N6297	CP517-2N6042-WS
2N6298	CP517-2N6053-CM
2N6298	CP517-2N6053-CT
CP517-BDX54C-CT	CP517-2N6296-CT
CP517-BDX54C-WS	CP517-2N6299-CT
CP517-PMD13K80-CT	CP517-2N6299-WS
CP517-TIP117-CT	CP517-2N6668-CT
CP517-TIP126-CT	CP517-2N6668-WS
CP517-TIP127-CT	CEN958
CP517-TIP127-WS	CEN1224